

BC237/238/239

Switching and Amplifier Applications • Low Noise: BC239



NPN Epitaxial Silicon Transistor

1. Collector 2. Base 3. Emitter

Absolute Maximum Ratings T_a=25°C unless otherwise noted

Symbol	Paramet	er	Value	Units
V _{CES}	Collector-Emitter Voltage	: BC237 : BC238/239	50 30	V V
V _{CEO}	Collector-Emitter Voltage	: BC237 : BC238/239	45 25	V V
V _{EBO}	Emitter-Base Voltage	: BC237 : BC238/239	6 5	V V
I _C	Collector Current (DC)		100	mA
P _C	Collector Power Dissipation		500	mW
TJ	Junction Temperature		150	°C
T _{STG}	Storage Temperature		-55 ~ 150	°C

$\textbf{Electrical Characteristics} \ \, \textbf{T}_{a} \!\!=\!\! 25^{\circ} \textbf{C} \ \, \text{unless otherwise noted}$

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV _{CEO}	Collector-Emitter Breakdown Voltage : BC237 : BC238/239	I _C =2mA, I _B =0	45 25			V
BV _{EBO}	Emitter Base Breakdown Voltage : BC237 : BC238/239	I _E =1μA, I _C =0	6 5			V
I _{CES}	Collector Cut-off Current : BC237 : BC238/239	V _{CE} =50V, V _{BE} =0 V _{CE} =30V, V _{BE} =0		0.2 0.2	15 15	nA nA
h _{FE}	DC Current Gain	V _{CE} =5V, I _C =2mA	120		800	
V _{CE} (sat)	Collector-Emitter Saturation Voltage	I_C =10mA, I_B =0.5mA I_C =100mA, I_B =5mA		0.07 0.2	0.2 0.6	V
V _{BE} (sat)	Collector-Base Saturation Voltage	I_C =10mA, I_B =0.5mA I_C =100mA, I_B =5mA		0.73 0.87	0.83 1.05	V
V _{BE} (on)	Base-Emitter On Voltage	V _{CE} =5V, I _C =2mA	0.55	0.62	0.7	V
f _T	Current Gain Bandwidth Product	V _{CE} =3V, I _C =0.5mA, f=100MHz V _{CE} =5V, I _C =10mA, f=100MHz	150	85 250		MHz MHz
C _{ob}	Output Capacitance	V _{CB} =10V, I _E =0, f=1MHz		3.5	6	pF
C _{ib}	Input Base Capacitance	V _{EB} =0.5V, I _C =0, f=1MHz		8		pF
NF	Noise Figure	$\begin{split} &V_{\text{CE}}\text{=}5\text{V, I}_{\text{C}}\text{=}0.2\text{mA,}\\ &\text{f=}1\text{KHz R}_{\text{G}}\text{=}2\text{K}\Omega\\ &V_{\text{CE}}\text{=}5\text{V, I}_{\text{C}}\text{=}0.2\text{mA}\\ &R_{\text{G}}\text{=}2\text{K}\Omega,\text{f=}30\text{\sim}15\text{KHz} \end{split}$		2	10 4 4	dB dB dB

h_{FE} Classification

Classification	А	В	С	
h _{FE}	120 ~ 220	180 ~ 460	380 ~ 800	

Typical Characteristics

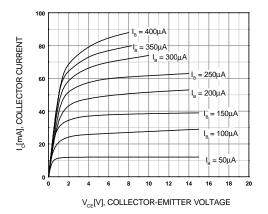


Figure 1. Static Characteristic

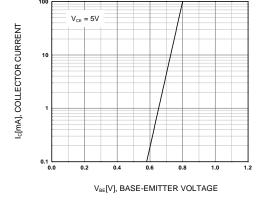


Figure 2. Transfer Characteristic

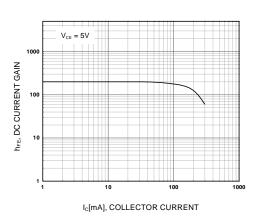


Figure 3. DC current Gain

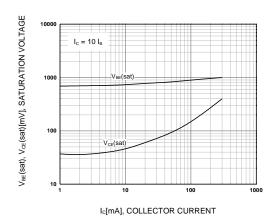


Figure 4. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

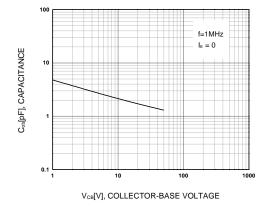


Figure 5. Output Capacitance

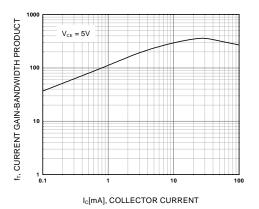
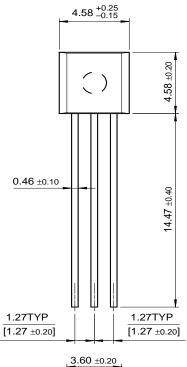
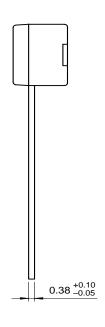


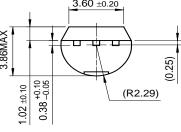
Figure 6. Current Gain Bandwidth Product

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EcoSPARK™	GTO™	MSX™	QT Optoelectronics™	TinyLogic™
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EnSigna™	I^2C^{TM}	OCX^{TM}	RapidConfigure™	UHC™
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